

500 Watts • 50 Volts • 450 μs, 35% 960 - 1215 MHz Broad Band Data Link

### GENERAL DESCRIPTION

The 0912GN-500LV is an internally matched, COMMON SOURCE, class AB GaN on SiC HEMT transistor capable of providing over 16dB gain, 500 Watts of pulsed RF output power at 450µs pulse width, 35% duty factor across the 960 to 1215 MHz band. The transistor has internal pre-match for optimal performance. This hermetically sealed transistor can be used for Broadband Data Link applications. It utilizes gold metallization and eutectic attach to provide highest reliability and superior ruggedness.

# 55-KR Common Source

### ABSOLUTE MAXIMUM RATINGS

**Maximum Power Dissipation** 

Device Dissipation @ 25°C

**Maximum Voltage and Current** 

Drain-Source Voltage (V<sub>DSS</sub>) 150 V Gate-Source Voltage (V<sub>GS</sub>) -8 to 0 V

**Maximum Temperatures** 

Storage Temperature ( $T_{STG}$ ) -55 to +125 °C Operating Junction Temperature +250 °C



### **ELECTRICAL CHARACTERISTICS @ 25°C**

Symbol	Characteristics	Test Conditions	Min	Тур	Max	Units
P <sub>OUT</sub>	Output Power	Freq=960, 1090, 1215 MHz	500	550		W
G <sub>P</sub>	Power Gain	Pin=12.5W, Freq=960,1090,1215MHz	16	16.5		dB
$\eta_{D}$	Drain Efficiency	Pin=12.5W, Freq=960,1090,1215MHz	60	63		%
Dr	Droop	Pin=12.5W, Freq=960,1090,1215MHz			0.5	dB
VSWR-T	Load Mismatch Tolerance	Pin=12.5W, Freq=1215MHz			3:1	
θ <sub>JC</sub>	Thermal Resistance	Pulse Width=450uS, Duty=35%			0.37	°C/W

Bias Condition: Vdd=+50V, Idg=100mA average current (Vgs= -2.0 ~ -4.5V) with constant gate bias

#### **FUNCTIONAL CHARACTERISTICS @ 25°C**

I <sub>D(Off)</sub>	Drain leakage current	$V_{gS} = -8V, V_D = 150V$		64	mA
$I_{G(Off)}$	Gate leakage current	$V_{gS} = -8V, V_D = 0V$		22	mA

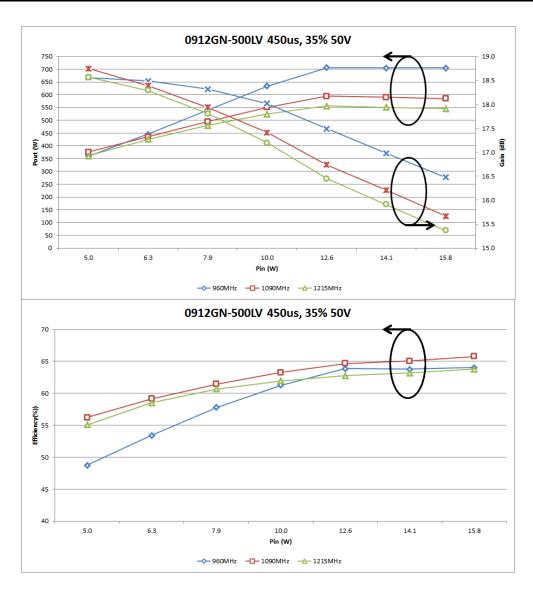
Export Classification: EAR-99



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### TYPICAL BROAD BAND PERFORMACE DATA

Frequency	P <sub>IN</sub> (W)	P <sub>OUT</sub> (W)	I <sub>D</sub> (A)	RL (dB)	η <sub>D</sub> (%)	G <sub>P</sub> (dB)	Droop (dB)
960 MHz	12.5	706	7.73	-7	64	17.5	0.41
1090 MHz	12.5	594	6.43	-6.5	65	16.7	0.29
1215 MHz	12.5	556	6.2	-10	63	16.5	0.24





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### TYPICAL DATA LINK BROAD BAND PERFORMACE

F	D (M)	P1*				P256*		<b>D</b>	
Freq	P <sub>IN</sub> (W)	P <sub>OUT</sub> (W)	G <sub>P</sub> (dB)	IRL (dB)	I <sub>D</sub> (mA)	Eff (%)	P <sub>OUT</sub> (W)	G <sub>P</sub> (dB)	Droop
Pulsing	Pulsing: 256 pulse burst - 6.4us @ 13µs, Burst Rep Rate=7.8125ms (21% Duty Cycle)								
960 MHz	10.0	604	17.8	-7.0	4650	55.5	550	17.4	0.41
1090 MHz	10.0	653	18.2	-9.2	4540	61.5	607	17.8	0.32
1215 MHz	10.0	659	18.2	-7.7	4340	65.0	618	17.9	0.28
Pulsing	Pulsing: 444 pulse burst - 6.4us @ 13µs, Burst Rep Rate=5777.4ms (49% Duty Cycle)								
960 MHz	10.0	579	17.6	-7.0	4580	53.5	532	17.3	0.37
1090 MHz	10.0	640	18.1	-9.2	4510	60.0	601	17.8	0.27
1215 MHz	10.0	646	18.1	-7.7	4330	63.1	614	17.9	0.22

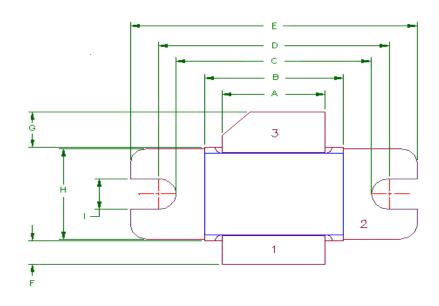
 $V_{DD} = 50V$ ,  $V_{GS} = -3.61V$ ,  $I_{DQ} = 100mA$ 

<sup>\*</sup>pulse power measured at pulse center, 3.2us from rising edge



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### 55-KR PACKAGE DIMENSION







1	=	Gate
2	=	Source
3	=	Drain

Dimension	Min (mil)	Min (mm)	Max (mil)	Max (mm)
Α	370	9.40	372	9.44
В	498	12.65	500	12.7
С	700	17.78	702	17.83
D	830	21.08	832	21.13
E	1030	26.16	1032	26.21
F	101	2.56	102	2.59
G	151	3.84	152	3.86
Н	385	9.78	387	9.83
I	130	3.30	132	3.35
J	003	.076	004	0.10
K	135	3.43	137	3.48
L	105	2.67	107	2.72
M	085	2.16	86	2.18
N	065	1.65	66	1.68



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#### **Revision History**

Revision Level / Date	Para. Affected	Description
01 / June 2013	-	Initial Preliminary Release

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